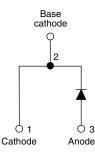
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 30 A



www.vishay.com



PRIMARY CHARACTERISTICS				
I _{F(AV)}	30 A			
V _R	1200 V			
V _F at I _F	2.3 V			
t _{rr} typ.	47 ns			
T _J max.	150 °C			
Package	TO-247AC 2L			
Circuit configuration	Single			

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Designed and qualified according to ${\sf JEDEC}^{\circledast}\text{-}{\sf JESD}$ 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

VS-HFA30PB120... is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 30 A continuous current, the VS-HFA30PB120... is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30PB120... is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V _R		1200	V		
Maximum continuous forward current	١ _F	T _C = 100 °C	30			
Single pulse forward current	I _{FSM}	t _p = 10 ms	120	А		
Maximum repetitive forward current	I _{FRM}		90			
Maximum power dissipation	P _D	T _C = 25 °C	350	W		
Maximum power dissipation		T _C = 100 °C	140	vv		
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C		

RoHS COMPLIANT HALOGEN FREE

Revision: 29-Nov-2019

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



www.vishay.com

Vishay Semiconductors

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		1200	-	-	
		I _F = 30 A		-	2.4	4.1	v
Maximum forward voltage V _{FM}	I _F = 60 A	See fig. 1	-	3.1	5.7		
		I _F = 30 A, T _J = 125 °C		-	2.3	4.0	
Maximum reverse		$V_R = V_R$ rated	See fig. 0	-	1.3	40	
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	See fig. 2	-	1100	4000	μA
Junction capacitance	CT	V _R = 200 V See fig. 3		-	50	75	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0 - nl				nH	

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	47	-	
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C		-	110	170	ns
000 lig. 0, 10	t _{rr2}	T _J = 125 °C	C - 170	170	260		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	10	15	A
See fig. 6	I _{RRM2}	T _J = 125 °C	I _F = 30 A	-	16	24	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	dl _F /dt = 200 A/µs	-	650	980	nC
See fig. 7	Q _{rr2}	T _J = 125 °C	V _R = 200 V	-	1540	2310	no
Peak rate of fall of recovery	dl _{(rec)M} /dt1	T _J = 25 °C]	-	270	-	A/µs
current during t _b See fig. 8	dl _{(rec)M} /dt2	T _J = 125 °C		-	240	-	Αγμδ

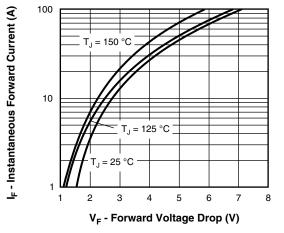
THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	0.36	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.50	-	
Weight			-	5.61	-	g
weight			-	0.198	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC 2L	HFA30PB120			

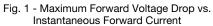
Revision: 29-Nov-2019

Document Number: 94069



Vishay Semiconductors





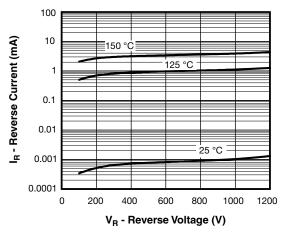


Fig. 2 - Typical Reverse Current vs. Reverse Voltage

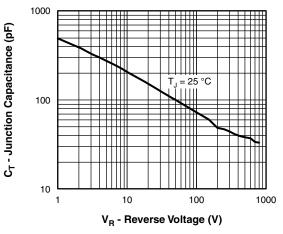


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

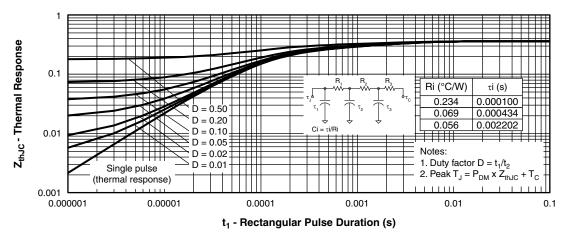


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

 Revision: 29-Nov-2019
 3
 Document Number: 94069

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



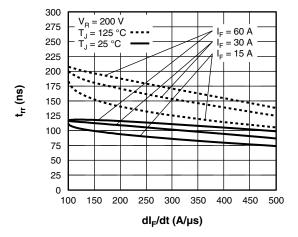


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt (Per Leg)

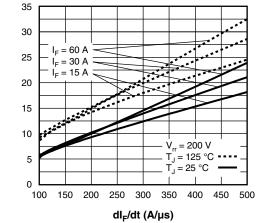
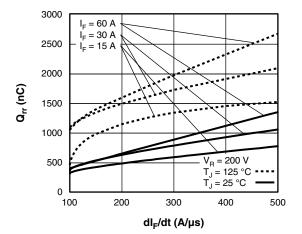


Fig. 6 - Typical Recovery Current vs. dl_F/dt (Per Leg)



Vishay Semiconductors

Fig. 7 - Typical Stored Charge vs. dl_F/dt (Per Leg)

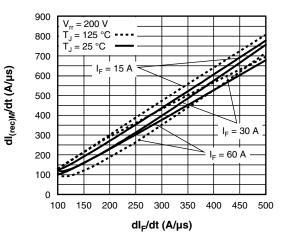


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt (Per Leg)

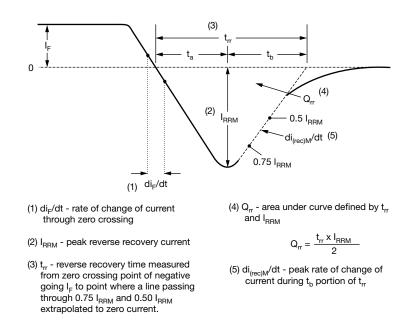


Fig. 9 - Reverse Recovery Waveform and Definitions

Revision: 29-Nov-2019	4	Document Number: 94069
For technical questions within your region:	DiodesAmericas@vishay.com, DiodesAsia@vish	<u>ay.com, DiodesEurope@vishay.com</u>
	E WITHOUT NOTICE. THE PRODUCTS DESCRI	
ARE SUBJECT TO SPEC	CIFIC DISCLAIMERS, SET FORTH AT <u>www.visha</u>	<u>y.com/doc?91000</u>

I_{RRM} (A)



www.vishay.com

ORDERING INFORMATION TABLE

Device code	VS-	HF	Α	30	РВ	120	-N3
		2	3	4	5	6	7
	1 - 2 - 3 - 4 - 5 - 6 - 7 -	HE: Electric Cur B Voltric Env	XFRED [®] ctron irra rent rati = TO-24 age rati ironmer	-	= 30 A) pins) = 1200) V)	

ORDERING INFORMATION (Example)						
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION			
VS-HFA30PB120-N3	25	500	Antistatic plastic tube			

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?96144			
Part marking information www.vishay.com/doc?95648				



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.